# MXD8015H

## Low Noise Amplifier for LTE Mid-High Band


## General Description

MXD8015H high gain, low noise amplifier (LNA) is dedicated to LTE middle band and high band receive using advanced RFCMOS process. The high linearity performance and low noise figure makes the device an ideal choice for LTE receiving Applications.

MXD8015H works under a 1.6V to 3.3V single power supply while consumes 6 mA current in low noise mode, in power down mode, the power consumption will be reduced to less than 1uA.

MXD8015H uses a small 1.1mm × 0.7mm × 0.45mm LGA 6-pin package.

## Applications

- LTE high-mid band receiving

## Features

- Broadband frequency range: 1.8 to 2.7 GHz
- High Gain
  - 15.5dB gain at 1.8GHz to 2.2GHz
  - 14.5dB gain at 2.3GHz to 2.7GHz
- Low noise figure
  - 0.65dB noise figure at 1.8GHz to 2.2GHz
  - 0.70dB noise figure at 2.3GHz to 2.7GHz
- Operation current 6mA
- Small, LGA (6-pin, 1.1mm x 0.7mm x 0.45mm) package , MSL1
- No DC blocking capacitors required.

## Pin Configuration/Application Diagram (Top view)

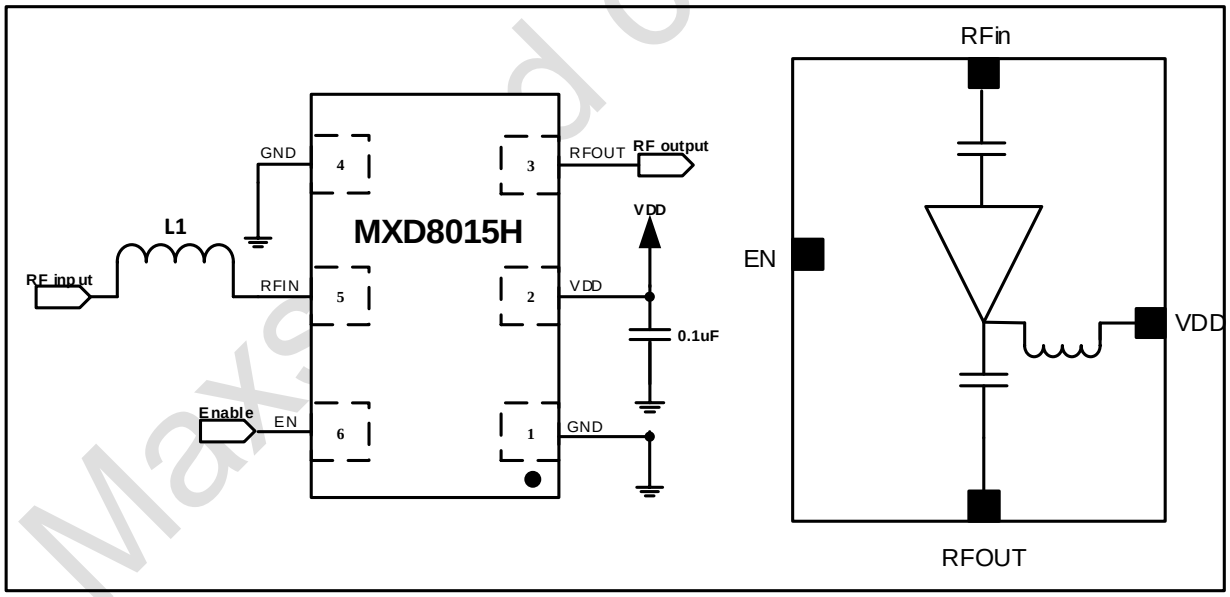



**Figure 1 MXD8015H application circuit**

## Pin Descriptions & Input matching inductance

**Table 1**

| Pin | Pin Name | I/O | Pin Description |
|---|---|---|---|
| 1 | GND | AG | Analog VSS |
| 2 | VDD | AP | Power supply |
| 3 | RFOUT | AO | LNA output |
| 4 | GND | AG | Analog VSS |
| 5 | RFIN | AI | LNA input from antenna |
| 6 | EN | DI | Pull high into low noise mode, pull low into power down mode |

**Note:** *DI* (digital input), *DO* (digital output), *DIO* (digital bidirectional), *AI* (analog input), *AO* (analog output), *AIO* (analog bidirectional), *AP* (analog power), *AG* (analog ground),

**Table 2 Input matching inductance**

| Component | Matching Band | Vendor | Type | Part Number & value |
|---|---|---|---|---|
| L1 | 1800MHz – 2200MHz | Murata | Wired inductor, high Q | LQW15AN6N8, 6.8nH |
| | | various | Ceramic inductor, low Q | 6.2nH |
| | 2300MHz – 2700MHz | Murata | Wired inductor, high Q | LQW15AN4N3, 4.3nH |
| | | various | Ceramic inductor, low Q | 3.9nH |

## Recommended Operation Range

**Table 3**

| Parameters | Symbol | Min | Typ | Max | Units |
|---|---|---|---|---|---|
| Operation Frequency | f1 | 1800 | - | 2700 | MHz |
| Power supply | $V_{DD}$ | 1.6 | 2.8 | 3.3 | V |
| Control Voltage High | $V_{CTL\_H}$ | 1.0 | 1.8 | VDD | V |
| Control Voltage Low | $V_{CTL\_L}$ | 0 | 0 | 0.3 | V |

## Absolute Maximum Ratings

**Table 4 Maximum ratings**

| Parameters | Symbol | Minimum | Maximum | Units |
|---|---|---|---|---|
| Supply voltage | $V_{DD}$ | -0.3 | +3.6 | V |
| Digital control voltage | $V_{CTL}$ | -0.3 | VDD+0.3 | V |
| RF input power | $P_{IN}$ | - | +20 | dBm |
| Operating temperature | $T_{OP}$ | –40 | +90 | ℃ |
| Storage temperature | $T_{STG}$ | –65 | +160 | ℃ |
| Electrostatic Discharge<br>Human body model (HBM), Class 1C[Note1]<br>Machine Model (MM), Class A[Note2]<br>Charged device model (CDM), Class III[Note3] | <br>ESD_HBM<br>ESD_MM<br>ESD_CDM | <br><br>- | <br>1500<br>125<br>500 | <br><br>V |

**Note:** Exposure to maximum rating conditions for extended periods may reduce device reliability. There is no damage to device with only one parameter set at the limit and all other parameters set at or below their nominal value. Exceeding any of the limits listed here may result in permanent damage to the device.
**Note1**: According to ESDA/JEDECJS-001-2014
**Note2**: According to JESD22-A115C
**Note3**: According to ESDA/JEDECJS-002-2014

## Specifications

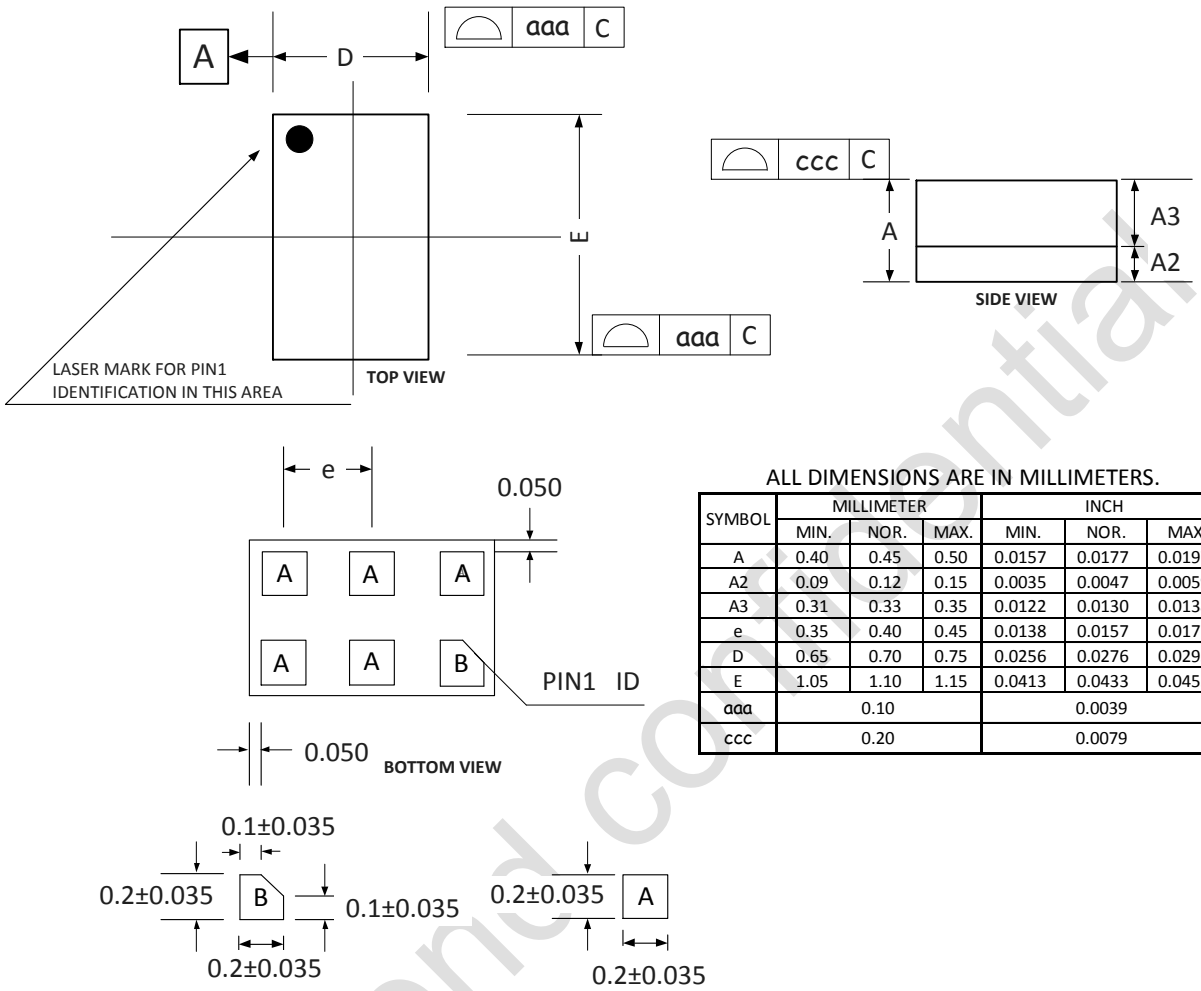
Typically $T_A$=25℃ VDD=2.8V, All data measured on Maxscend's EVB, unless otherwise noted

**Table 5 High Gain mode Electrical Specifications**

| Parameter | Symbol | Specification | | | Units | Test Condition |
|---|---|---|---|---|---|---|
| | | Min. | Typical | Max. | | |
| **DC Specifications** | | | | | | |
| Supply voltage | $V_{DD}$ | 1.6 | 2.8 | 3.3 | V | |
| Supply current | $I_{DD}$ | 4<br>0 | 6<br>0.05 | 9<br>1 | mA<br>uA | $V_{DD}$ = 2.8V, $V_{EN}$=high<br>$V_{DD}$ = 2.8 V, $V_{EN}$=low |
| **RF Specifications** | | | | | | |
| Power gain | G | 14<br>12.5 | 15.5<br>14.5 | 17<br>16.5 | dB<br>dB | 1800-2200MHz<br>2300-2700MHz |
| Noise figure | NF | - | 0.65<br>0.70 | 1.1<br>1.3 | dB<br>dB | 1800-2200MHz<br>2300-2700MHz |
| Input Return loss | \|S11\| | - | -10 | -5 | dB | 1800 to 2700MHz |
| Output Return loss | \|S22\| | - | -10 | -6 | dB | 1800 to 2700MHz |
| Stability factor | Kf | 1.2 | - | - | | |
| Input 1 dB compression point | P1dB | -10<br>-5 | -7<br>-2 | - | dBm<br>dBm | 1800 to 2200MHz<br>2300 to 2700MHz |
| Input IP3 | IIP3 | -4<br>-1 | 0<br>3 | - | dBm<br>dBm | Note1<br>Note2 |
| Startup time | | - | - | 1 | us | Shutdown state to power on state |

**Note1: Pin=Pin2=-25dBm, F1=2100MHz, F2=2101MHz**
**Note2: Pin=Pin2=-25dBm, F1=2600MHz, F2=2601MHz**

## Package Outline Dimensions




ALL DIMENSIONS ARE IN MILLIMETERS.

| SYMBOL | MILLIMETER | | | INCH | | |
|---|---|---|---|---|---|---|
| | MIN. | NOR. | MAX. | MIN. | NOR. | MAX. |
| A | 0.40 | 0.45 | 0.50 | 0.0157 | 0.0177 | 0.0197 |
| A2 | 0.09 | 0.12 | 0.15 | 0.0035 | 0.0047 | 0.0059 |
| A3 | 0.31 | 0.33 | 0.35 | 0.0122 | 0.0130 | 0.0138 |
| e | 0.35 | 0.40 | 0.45 | 0.0138 | 0.0157 | 0.0177 |
| D | 0.65 | 0.70 | 0.75 | 0.0256 | 0.0276 | 0.0295 |
| E | 1.05 | 1.10 | 1.15 | 0.0413 | 0.0433 | 0.0453 |
| aaa | 0.10 | | | 0.0039 | | |
| ccc | 0.20 | | | 0.0079 | | |

**Figure 2 MXD8015H outline dimension**

## Marking Specification

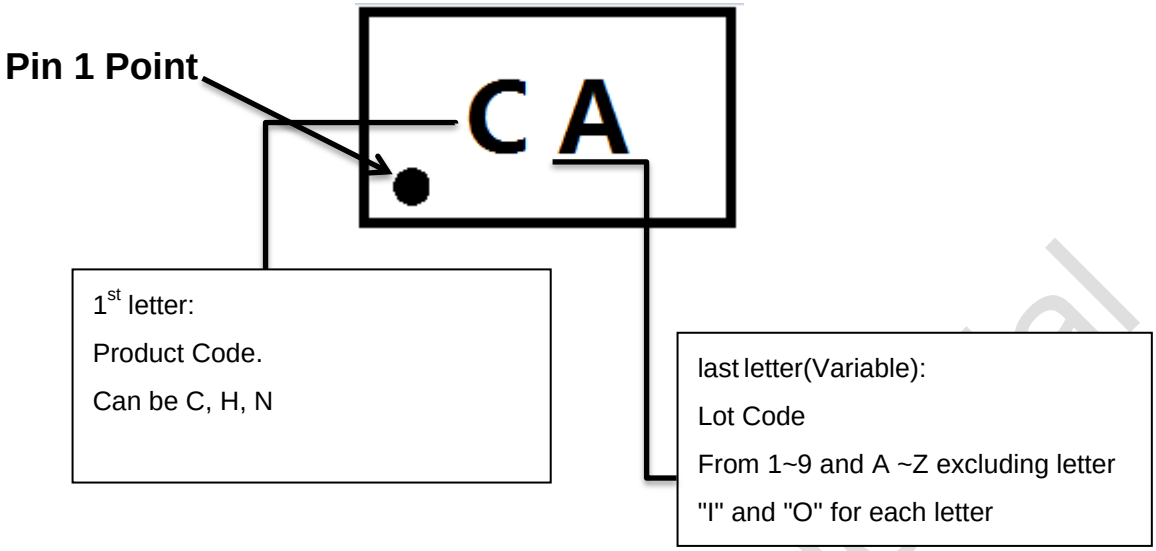
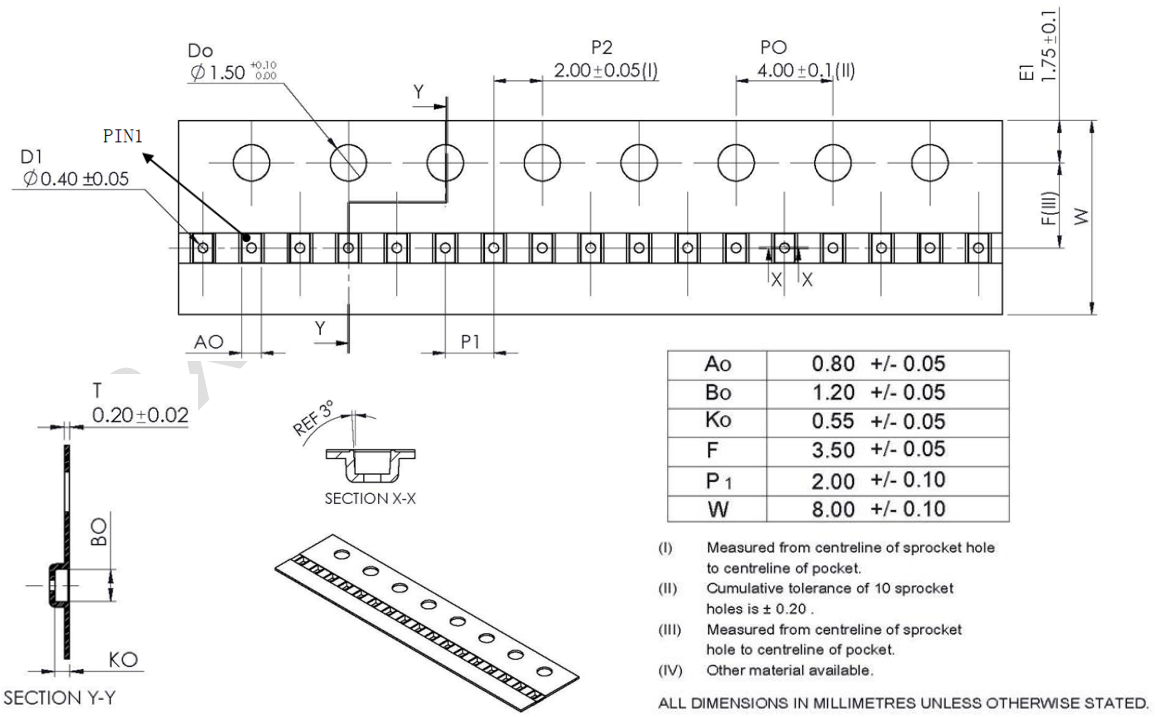



**Figure 3 Marking specification (Top View)**

## Tape and Reel Dimensions




| | |
|---|---|
| Ao | 0.80 +/- 0.05 |
| Bo | 1.20 +/- 0.05 |
| Ko | 0.55 +/- 0.05 |
| F | 3.50 +/- 0.05 |
| P 1 | 2.00 +/- 0.10 |
| W | 8.00 +/- 0.10 |

**Figure 4 Tape and reel dimensions**

## Reflow Chart

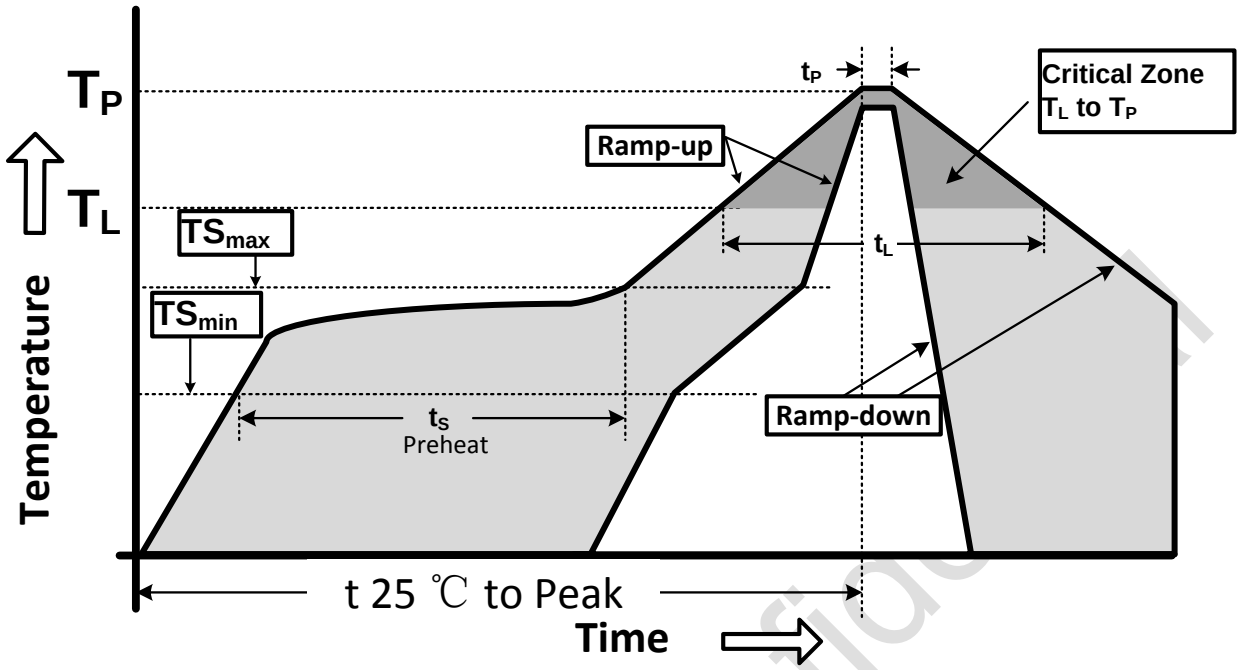



**Figure 5 Recommended Lead-Free Reflow Profile**

**Table 6 Reflow condition**

| Profile Parameter | Lead-Free Assembly, Convection, IR/Convection |
|---|---|
| Ramp-up rate（$TS_{max}$ to $T_p$） | 3℃/second max. |
| Preheat temperature（$TS_{min}$ to $TS_{max}$） | 150℃ to 200℃ |
| Preheat time（$t_s$） | 60 - 180 seconds |
| Time above TL , 217℃（$t_L$） | 60 - 150 seconds |
| Peak temperature（$T_p$） | 260℃ |
| Time within 5℃ of peak temperature($t_p$) | 20 - 40 seconds |
| Ramp-down rate | 6℃/second max. |
| Time 25℃ to peak temperature | 8 minutes max. |

## ESD Sensitivity

Integrated circuits are ESD sensitive and can be damaged by static electric charge. Proper ESD protection techniques should be used when handling these devices.

## RoHS Compliant

This product does not contain lead, mercury, cadmium, hexavalent chromium, polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE), and are considered RoHS compliant.